

Advanced Protected Fan-In WLCSP

13 Oct 2021

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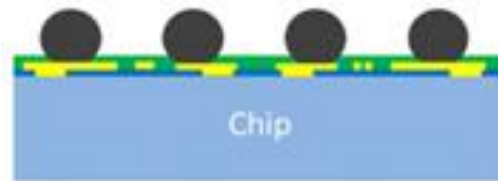
Ed Prack PhD
MASIP LLC

1. A brief recap of CSP evolution and PSB
2. CSP FI, and FO and as a CSP process alternative
3. 2-side Protected WLCSP
4. 6-side Protected CSP (P-WLCSP)
 1. Thinnest fully protected CSP
 2. Lowest Cost fully protected CSP
5. P-WLCSP to SiP and the future

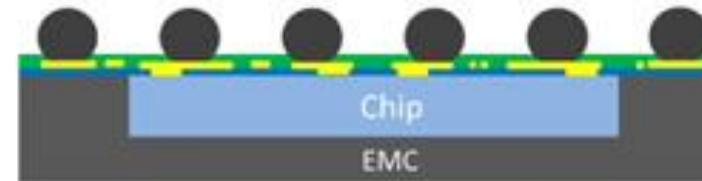
- WLCSP
 - ▶ With the advent of bumped die, new IC packages evolved
 - ▶ Low IO WLCSP, High IO FC (flip chip), CBGA (ceramic ball grid array) and PBGA (plastic BGA)
 - ▶ Reliability for bumped die packages evolved differently for high and low IO bumped die
- Active side protection became important with the entry of high IO die
 - ▶ Bumps on traditional final passivation resulted in unacceptable reliability
 - ▶ Addressed with a BEOL (back end of line) FAB application of PSB (passivation stress buffer)
 - ▶ PSB was used earlier to protect molded die surfaces from the filler particles in the mold compound (filled epoxies) encapsulants in traditional plastic IC packages for WB (wire bond) devices
 - ▶ CBGA and PBGA packages also included encapsulants, including filled epoxies, to protect the rest of the die and the bumps to improve reliability

- Low IO WLCSP (aka Fan In) was built on wafers adding bumps and redistributing the pads as needed.
 - ▶ This resulted in the die being the package
 - ▶ **However, without active side protection reliability issues ensued**
 - ▶ To maintain wafer processing active side protection options were needed
 - ▶ One option was to build the components of a plastic package on the active side on the wafer
 - ▶ A simpler (lower cost) option was to use PSB as used on FC wafers for high IO BGA packages
 - ▶ The PSB approach provided acceptable performance, **initially...**

- As devices became more complex, reliability requirements increased
 - PSB based processes no longer provided the required reliability
 - Higher IO capability and better reliability evolved to non-WL CSP
 - Larger area was needed for bump distribution, as well as, additional protection for the rest of die



(a) WLCSP Packaging



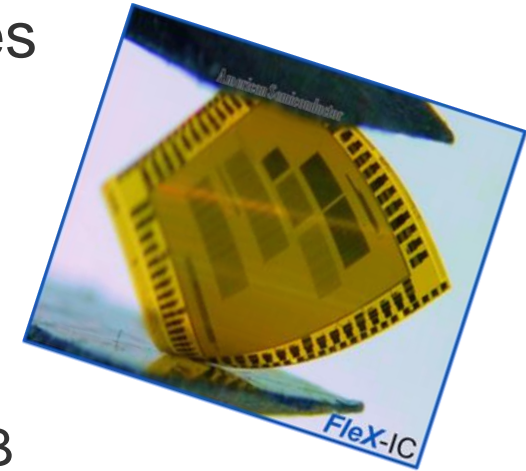
(b) Fan-out Packaging

WLCSP vs CSP FO. Source: Semiconductor Engineering Aug. 19, 2021

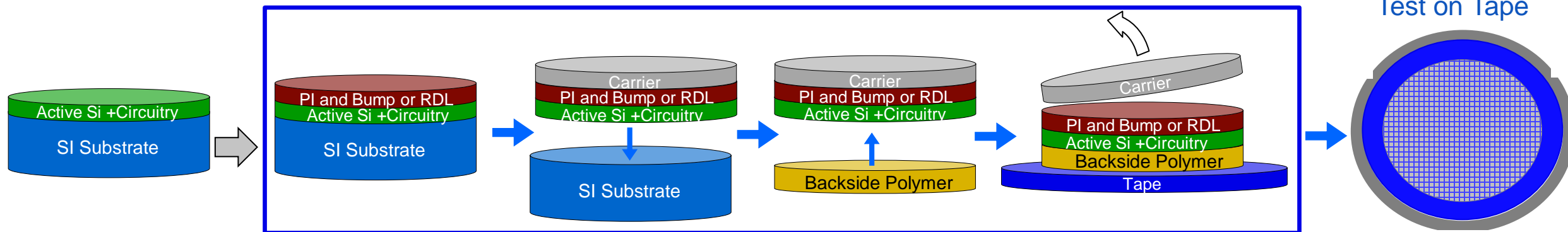
- Small FO packaging processes were used to produce non-WL CSP
 - 6-side protected CSP (all 6 sides with similar material) was implemented using FO processes such as M-series
 - FO for CSP includes die reconstitution, expensive tapes, molding operations, etc.
 - Resolving the reliability issues of unprotected die justified non-WL CSP for FI, but the added cost and process complexity was and is far from optimal

- A lower cost alternative
 - ▶ Retain the simplicity of PSB WLCSP while encasing all sides of the die in a PSB like material replacing the encapsulate materials in the non-WL CSP options
 - ▶ This requires several changes to allow all side coverage of the device with PSB material which then acts as the encapsulate for the package
 - ▶ Emerging thin wafer processing facilitates the ability to provide protection to more than just the active side of the die
 - ▶ Earlier presentations and papers on Semiconductor-on-Polymer™ (SoP) reported how this can be done for protecting the top and bottom of the die to improve mechanical reliability, as well as die performance, versus single sided or unprotected thin die

- 2-side protected packaging was the first step toward fully protected WLCSP
- 2-side protected FleX-C SoP is one example
 - ▶ Produced excellent mechanical reliability for thin silicon devices
 - ▶ Developed to overcome the mechanical reliability and yield issues associated with thin die
 - ▶ Implemented frontside and backside polyimide layers
 - Reduced die edge chipping and cracking common to thin die
 - First introduced to the Flexible Hybrid Electronics (FHE) market for FCB
 - Achieved the primary FHE goal of maintaining the thinnest assemblies possible
 - Beyond FHE, the technology is being applied in chip-on-flex applications where previous SMT resulted in poor formats and reliability issues associated with flex deformations



SoP Process Module



CMOS Wafer from any IDM or Foundry

Wafer Level Processing Technology

Temporary Carrier Bonding. Bulk Silicon removed (Silicon Substrate 10um)

Backside polymerization and stress balancing

SoP Wafer release and transfer to thermal Tape

Dicing on tape (High Speed Laser Dicing)

- Compatible with Standard Wafer Level processing
- Thin Wafer Completely supported through module
- Technology optimized to ensure flat wafer processing
- **Produces the thinnest ICs in the industry**
- **Currently supporting FHE and chip-on-flex applications**

SoP ICs Tape on Frame, or Tape & Reel, Gel Pack, or similar



Source epak.com

No thin wafer handling required in ultra-thin SoP process

Chip-on-flex Enablement

- Physical flexibility is maintained post assembly
- Eliminates flex shear problems
- Minimizes or eliminates mechanical failures at rigid/flex interfaces
- Demonstrated on PET, Paper and Cu-on-PI

| Thinning Method | Total Thickness (um) | Die Size (mm) | RoC Fail (mm) | Failure mode |
|-----------------------|----------------------|---------------|---------------|------------------|
| Conventional thinning | 300 | 5.0 X 5.0 | 30 | Delamination |
| | | 2.5 X 2.5 | 12 | Delamination |
| | 40 | 2.2 X 2.2 | 10 | Delam & Cracking |
| | 20 | 2.2 X 2.2 | 10 | Delam & Cracking |
| SoP WLCSP | 28um (Si<5um) | 2.5 x 2.5 | 5 | PASS |

Thinnest, Higher performance MultiChip Modules:

- Enhanced Thermal and Package uniformity
- Chip thickness matching using low cost polymer for improved multi-chip manufacturability
- Final Die-to-Die TTV performance < 2um

***RoC – Radius of curvature bending

SoP enables Ultra thin flex assemblies with no impact on devices

SoP on Pyralux® BLE flex demo



SoP on PET NFC flex demo

SoP NFC with battery < 1mm thick. 12.5mm RoC on vial.



Radius of Curvature (RoC) Testing– ICs on flex

This work sponsored in part by the Air Force Research Laboratory AFRL/RX

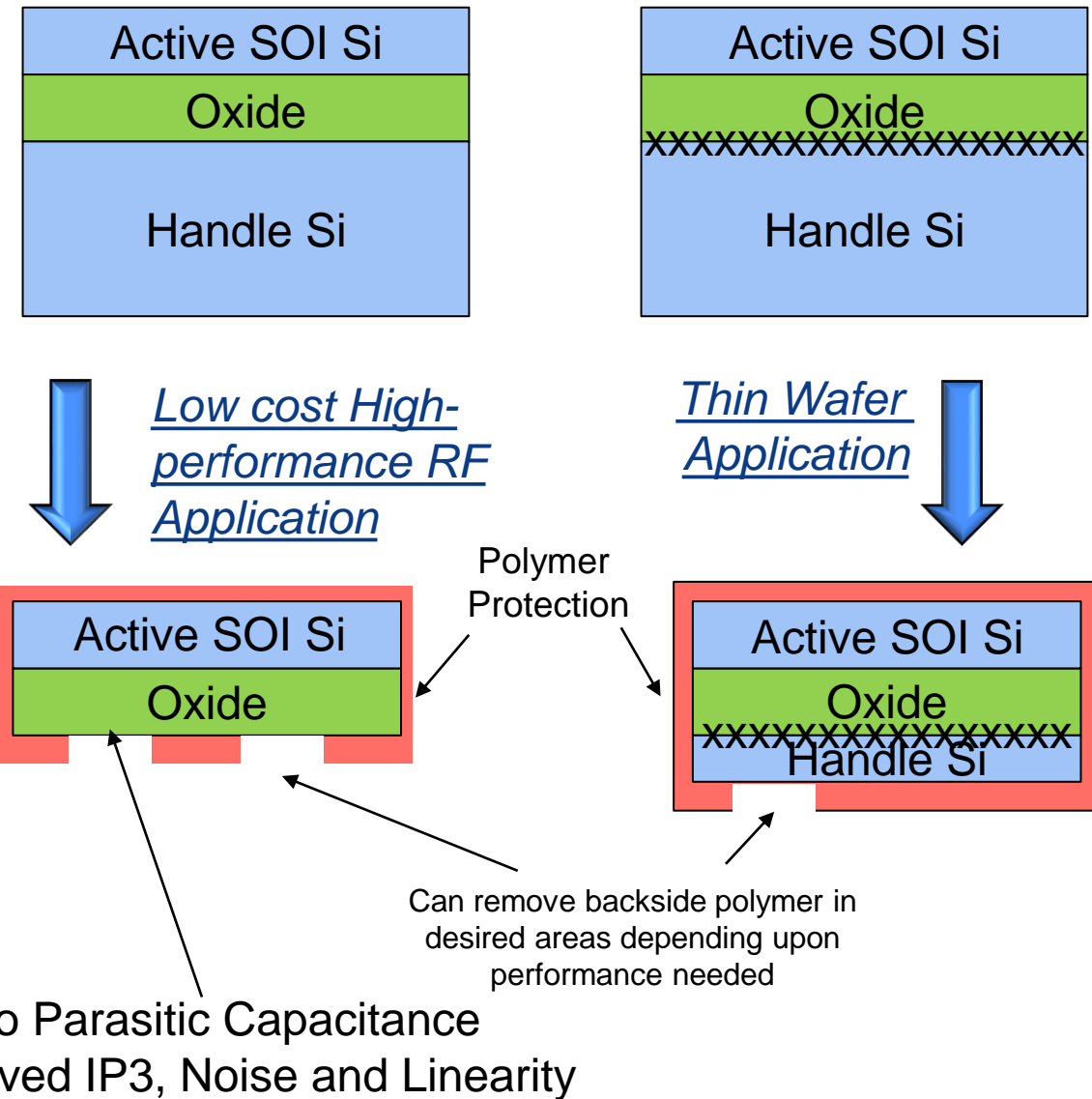


| Thinning Method | Total Thickness (um) | Die Size (mm) | RoC Fail (mm) | Failure mode |
|-----------------|----------------------|---------------|---------------|-----------------|
| Thin Die SOC | 35 Si | 2.16 X 2.28 | 10 | Crack |
| SoP ADC | <5 Si | 2.5 x 2.5 | 1 | PASS (ASI) |
| SoP SOC | <15 Si | 2.16 X 2.28 | <5 | PASS (Cypress) |
| SoP NFC | <15 Si | 2.51 X 2.51 | <5 | PASS (NXP) |
| SoP RFID | <15 Si | 1.66 X 2.05 | <5 | PASS (EM Micro) |

- SoP WLCSP may be most significant for RF devices that rely on SOI
 - ▶ The standard SoP process results in some amount of handle silicon remaining
 - The buried oxide/handle silicon interface is unchanged
 - Handle Si trap regions can be retained if desired.
 - However Rds can improve significantly with thinner handle silicon
 - ▶ SoP can be augmented for complete handle silicon removal
 - Eliminate substrate coupling capacitance
 - Low insertion loss backside PIs with $D_f < 0.003$ @ 80 Ghz can be used
 - ▶ Additionally, the backside encasement can be selectively removed
 - Key areas to further eliminate parasitic issue
 - Heat sink application

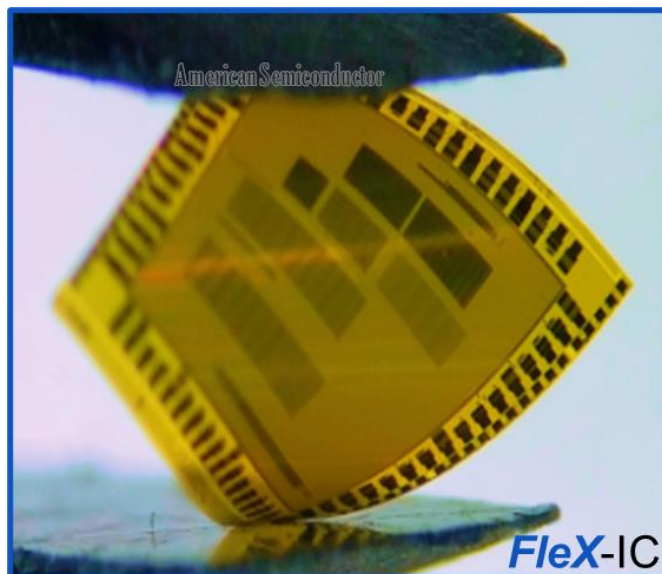
Silicon on Insulator – SoP options

- SoP process can be used on both Thin and Thick Film Silicon
 - Technology is independent of starting materials
- Can be used in two approaches depending upon need of device and application
 1. Thin Wafer Application
 - Ultra Thin applications – Standard process
 - Some amount of Silicon Handler wafer is still present
 - No need for redo of application circuits
 2. High performance RF Application - Elimination of Silicon Handling Wafer
 - No Substrate Coupling Capacitance
 - Low Insertion Loss backside PI available
 - $D_f < 0.003$ @ 80 Ghz and higher
 - Handle Si trap region can be retained if desired
 - Polymer can be selectively removed in key areas of device eliminating any parasitic issue
 - Applicable for new designs or existing products



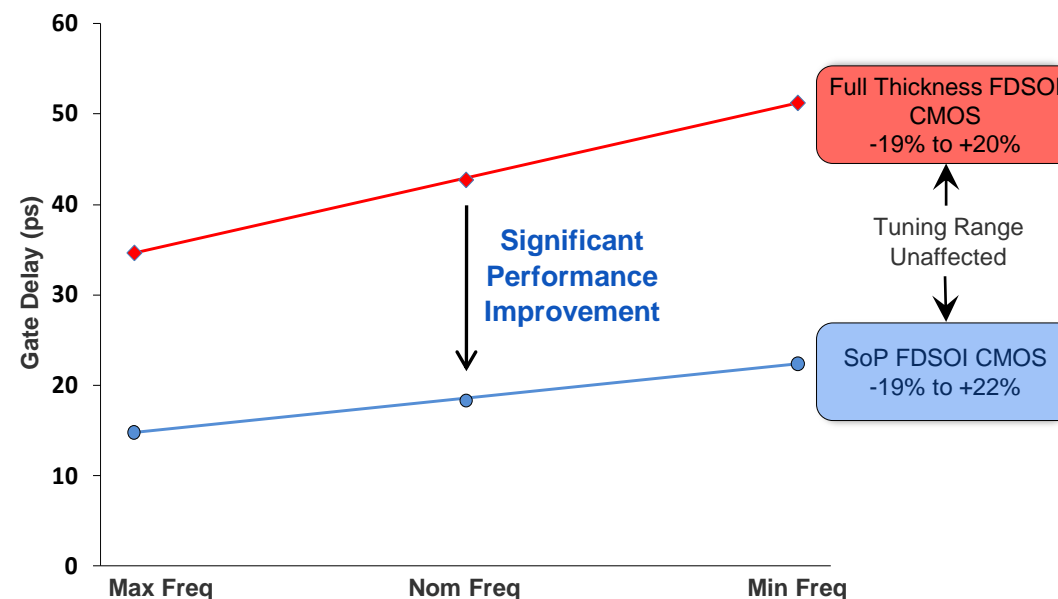
SoP FDSOI

- Handle Si fully removed
- Bottom junction capacitance eliminated
- Improved performance
- SOI thickness for sample: 2000Å



**SoP Flex-C Packaged
130nm FDSOI CMOS**

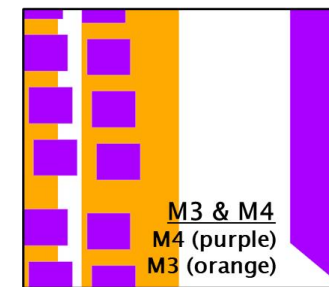
101-Stage Tunable Inverter Ring Oscillator Operating at 1.8V



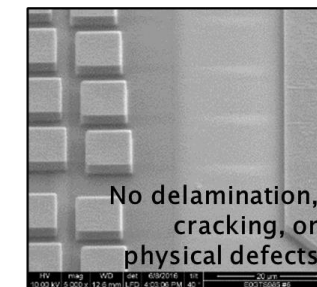
TESTING

HTOL 168 hours at 125C PASS
LTOL 168 at -25C PASS
ESD 4KV HBM PASS

Data Retention 150C non-bias PASS
Data Retention RoC PASS
Dynamic RoC >15k cycles PASS
Dynamic Torsion >90K cycles PASS



Layout View



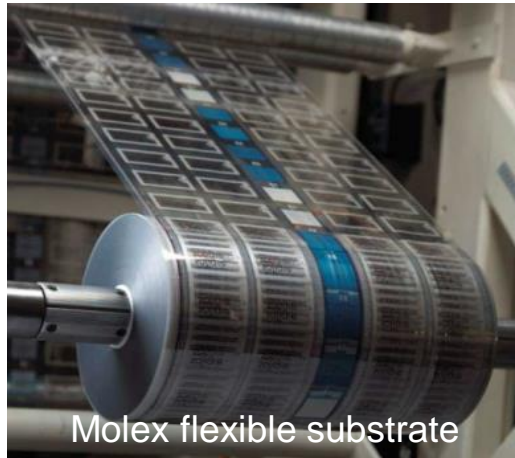
SEM Analysis

Note: Preliminary SoP results for Jazz CS180 PDSOI shows improved Q for ring oscillators

Flexible Hybrid System

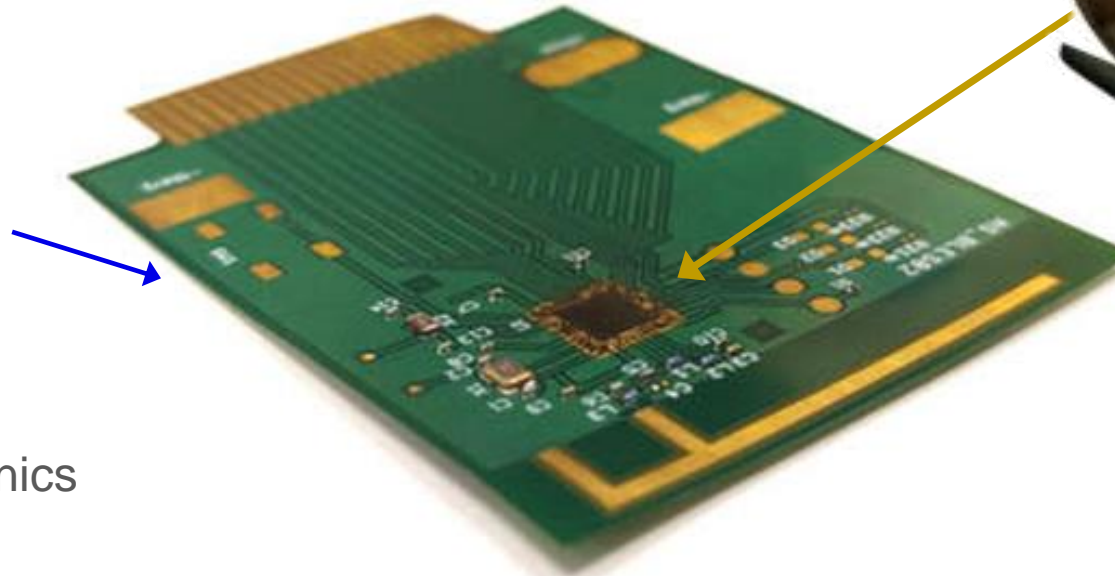
“Combining thin FCB and flexible silicon-based ICs creates a new class of flexible electronics.”

Flex or Printed Flexible Circuit Board (FCB)
R2R, S2S, Large Format

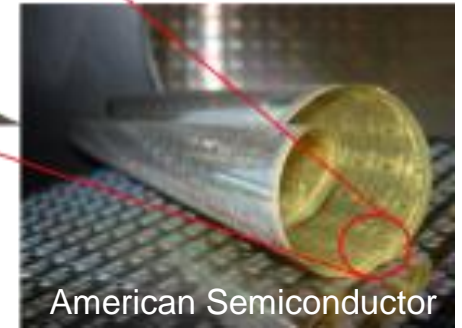


Flex and Printed Electronics

- Sensors
- Interconnects
- Antennas
- Displays
- Low Cost, Large Format
- Roll-To-Roll, Screen, Inkjet Print, ...



Ultra-thin SoP packaged *FleX*-ICs
High Performance, High Density



***FleX*-ICs**

- Bluetooth® SOC
- Data Processing
- Data Storage
- Communications
- Low Cost, High Performance
- ***FleX*** is a Semiconductor-on-Polymer (SoP) **chip scale packaging (CSP)** process.

Ultra-thin  Bluetooth®

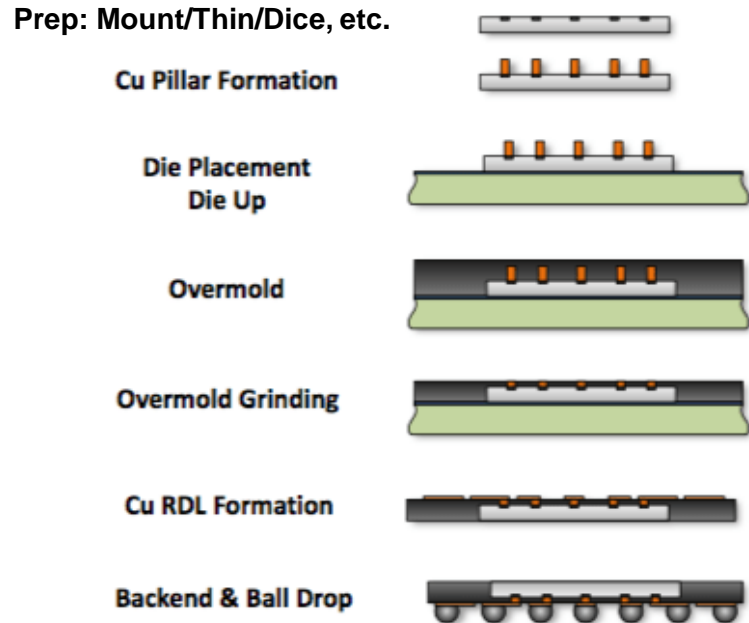
FleX-BLE Development Kit AS_DEVBLES02.kit

FHE enabling thinnerization

- “Protected WLCSP” or P-WLCSP
 - ▶ 6-side protection without the cost and complexity on non-WL FO type processes
 - ▶ P-WLCSP does not require pre-package die thinning, dicing or reconstitution
 - ▶ P-WLCSP Substantially reduce the equipment and process steps required for processing
 - ▶ Material reductions with the elimination of dicing tape and molding materials
- FleX-TM™ is a new SoP 6-side protected P-WLCSP process
 - ▶ Full protection, without the cost/complexity of non-WL FO processes used for protected CSP FI
 - ▶ 300mm process utilizes polyimide for encasement
 - ▶ The process includes maskless processing and high temperature temporary bonding
 - ▶ Enables use of a wide selection of PI for stress balancing
 - ▶ Final singulation (dicing) speed enhancement due to P-WLCSP PI scribe streets
- Enabling ultra-thin devices
 - ▶ Reduced die thickness improves capability for through silicon via (TSV) size and pitch
 - ▶ Enables high-temperature backside RDL (B-RDL) and heat sinks
 - ▶ CMOS silicon thicknesses is typically 10-15um, but can be adjusted as needed
 - ▶ SoP processing on SOI has demonstrated Si Tx at 2000A with SOI speed improvement

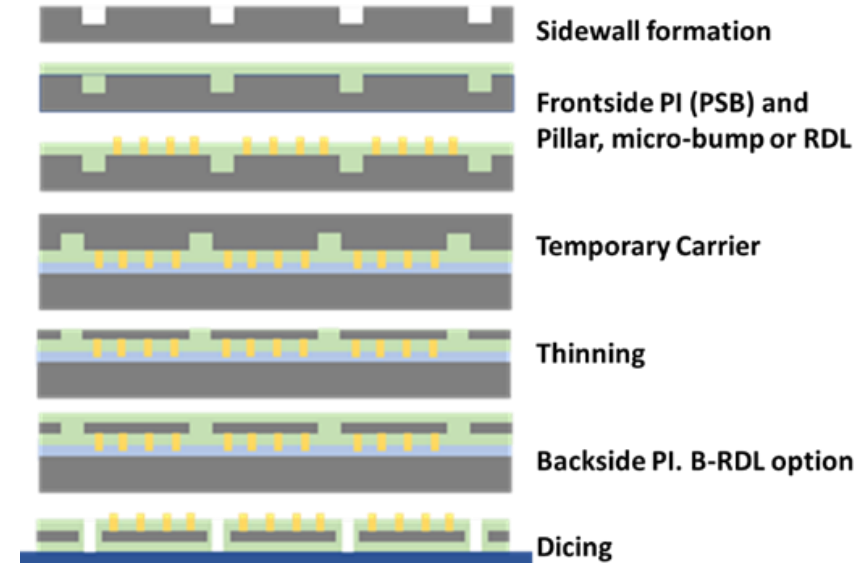
- Comparison of non-WL CSP and P-WLCSP SoP process provides an understanding of cost and complexity of protected packaging technology.

Die Up - M-Series



M-Series CSP FO Process. Source: SemiconductorEngineering Feb. 2018

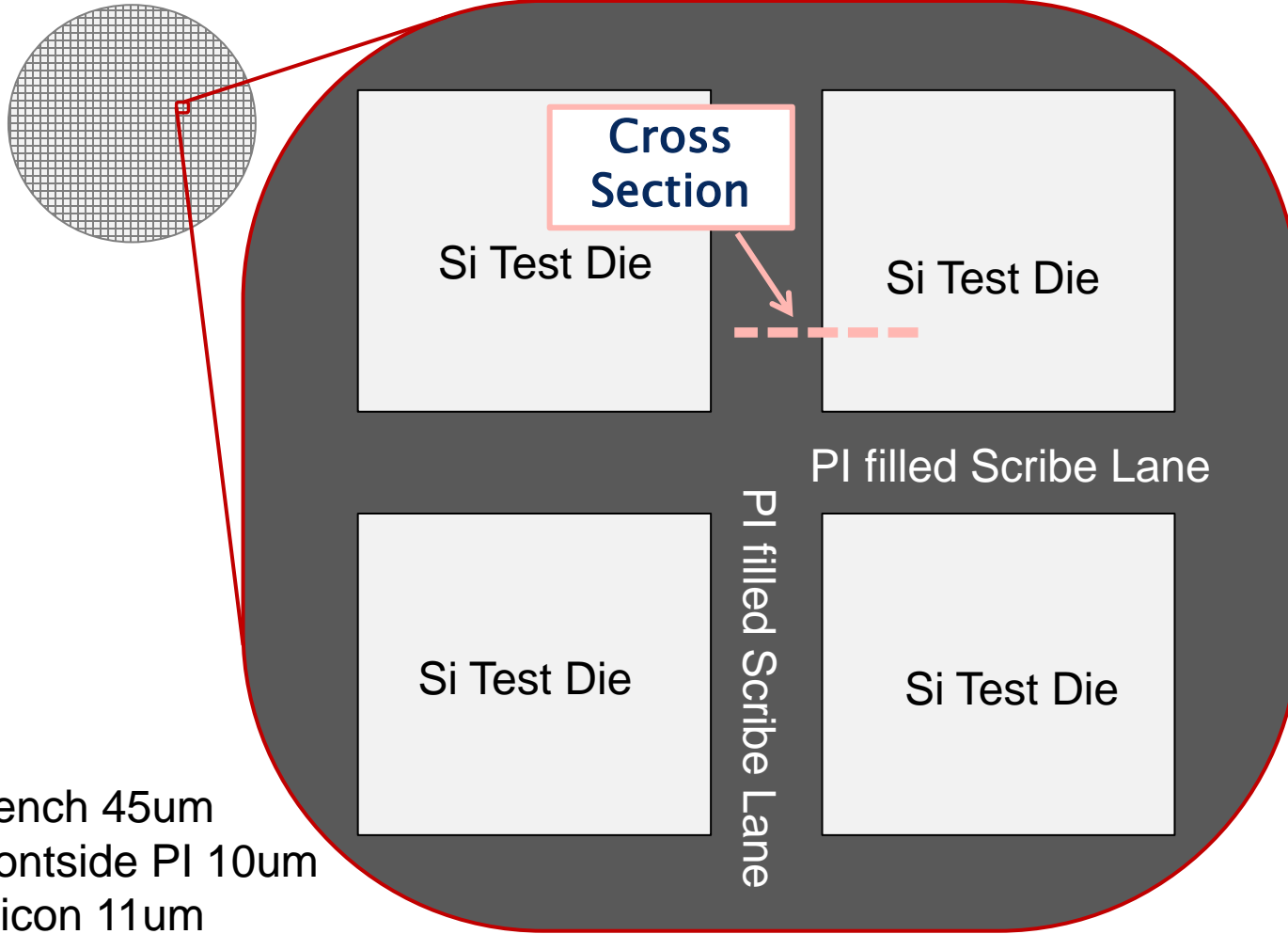
P-WLCSP – FleX-TM



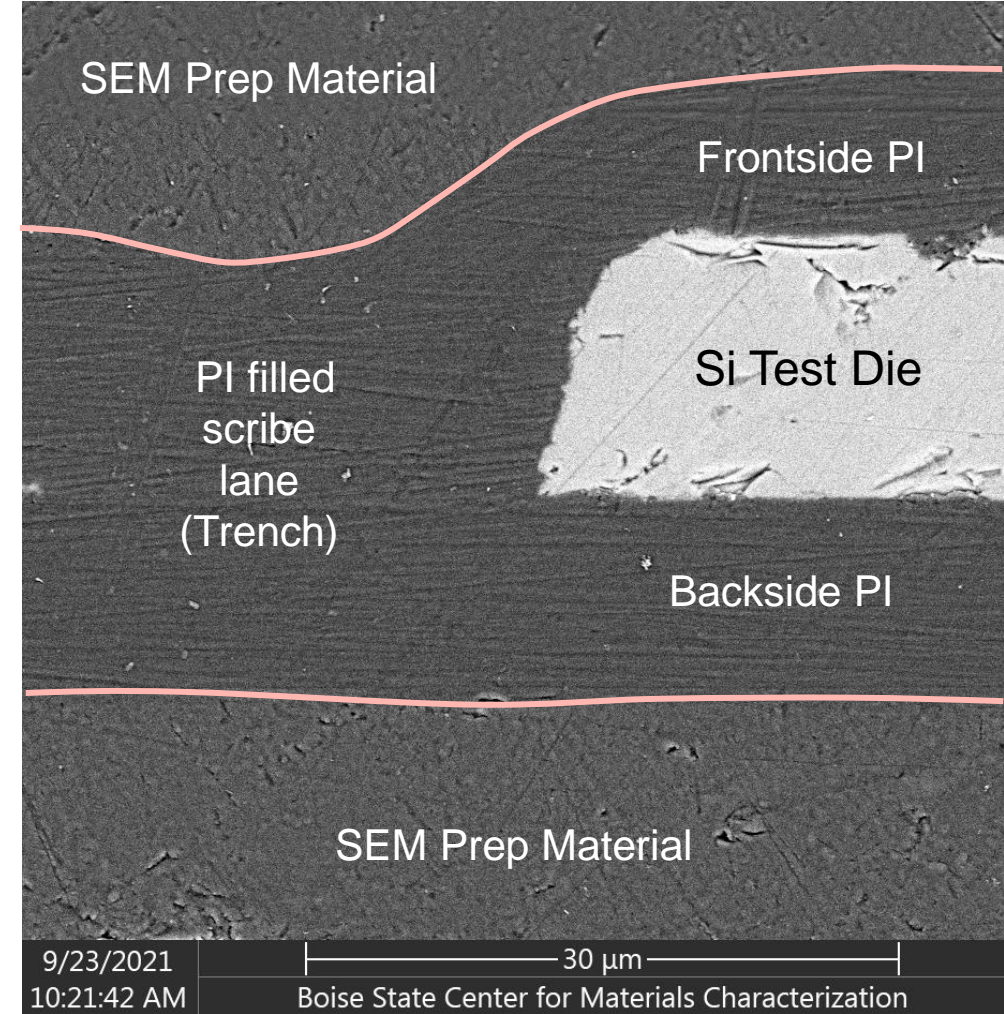
FleX-TM Protected WLCSP, U.S. Patent 9,082,881

- P-WLCSP processing provides cost reduction and performance improvement in CSP FI applications
- Produce robust ultra-thin devices for SiP applications - chipelets and heterogeneous integration
- Higher pin-counts and thinner board assemblies are macrotrends in modern electronics
- Reducing layer thicknesses, along with the opportunity to connect on top and bottom of die without any significant cost penalty is significant.

300mm Wafer



- Trench 45um
- Frontside PI 10um
- Silicon 11um
- Backside PI 10um
- Sidewall PI ~10um



SoP reduces processing steps and material usage for protected fan-in

- True wafer level CSP process (WLCSP) eliminates pre-packaging wafer prep:
 - ▶ No pre-package wafer grind
 - ▶ No pre-package singulation
 - ▶ No pre-package dicing tape
 - ▶ No pick-and-place for reconstitution
- Die reconstitution eliminated
- Maskless PSG
- Only 1 thinning step required – utilizes clean dry release temporary adhesive
- Low cost reusable silicon carrier wafer
- Only 1 singulation step required
- Only 1 tape layer
- Standard wafer level processing for bumps, pillars and/or RDL
- Overmold process eliminated

50% fewer steps → 50% less capital, or 2X capacity increase

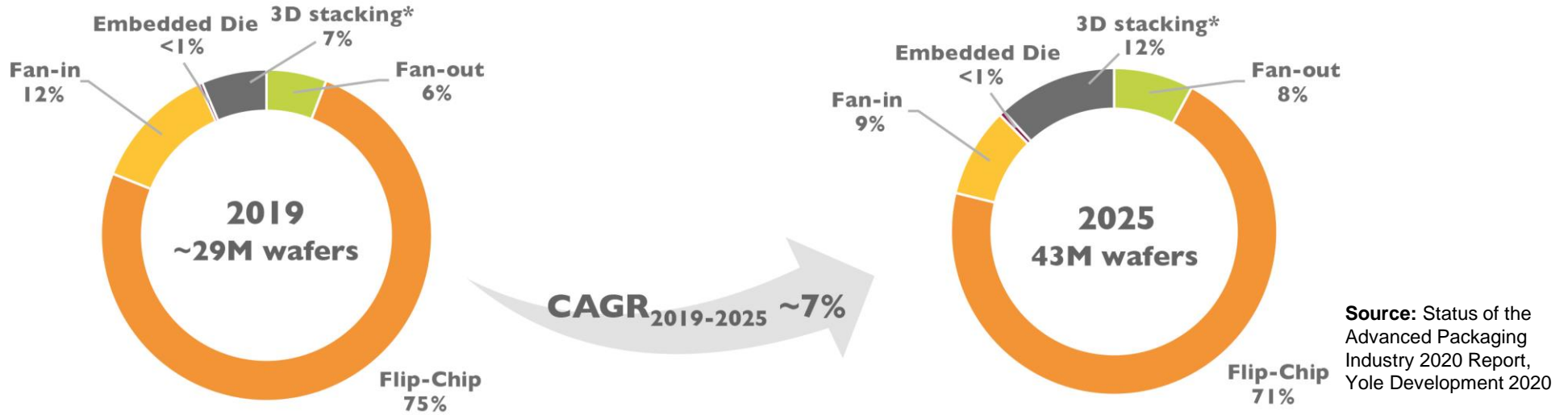
50% Less labor cost → Cycletime 50% less, improves cash flow

30-50% Less material cost

SoP – Lowest Cost Protected Fan-In

Direction for SoP FleX-TM: \$2B TAM -> \$36B by 2025

Market Forecasts



2019-2025 WLCSP/Fan-In package revenue evolution \$2B 2019- \$2.5B 2025 – Yole Development Nov. 2020

Advanced Packaging \$25.6B expected to reach \$36.3B by 2025, CAGR 7.8% – Yole Development Dec. 2020

Heterogeneous Integration projected to grow to 54 billion packages by 2025 – IMAPS/TechSearch Mar. 2021

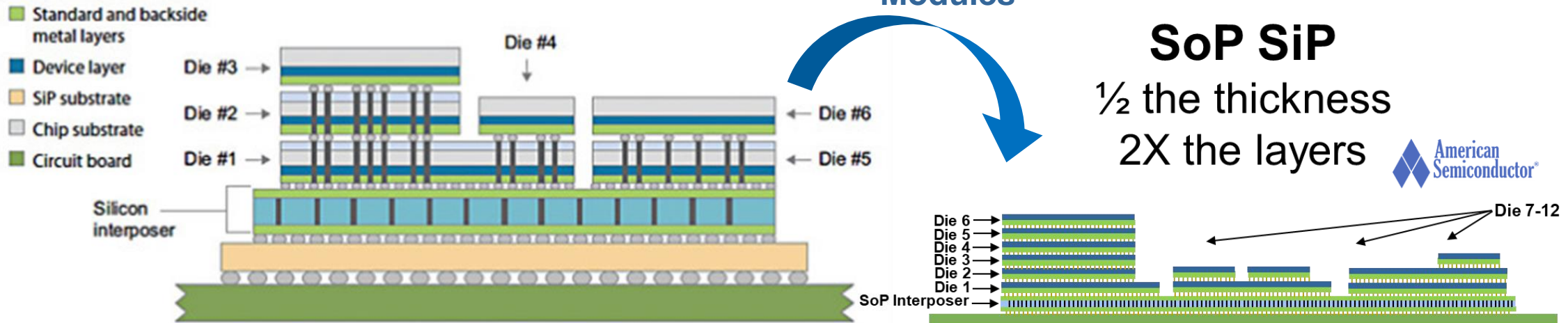
Packages using chiplets expected to show a CAGR of 104% from 2020 to 2025 – IMAPS/TechSearch Mar. 2021

Vision for P-WLCSP Advanced Packaging

3D, HI, Chiplet,
Modules

SoP SiP

1/2 the thickness
2X the layers



Source: Tech Design Forum May 8, 2018

- Thin, protected, ICs (SoP)
- Fully protected CSP for high yield
- Device performance improvements
- Thinner, finer pitch interposers
- High density TSV
- Direct Interconnect

- Added IC count without larger package
- Multi-function modules
- Sensor and Passive device integration
- Wireless
- Maskless
- Highest value add

- Full die protection has been widely adopted for reliability in FO, but with a high cost
- P-WLSCP SoP provides full die protection AND retains the simplicity of WLCSP with low cost
- FleX-TM SoP includes similar material on all 6 sides, minimizing uneven stress on the die
 - Reliability
 - Performance
- Continued P-WLCSP progress relies on further package reliability testing
- The next step requires collaboration with device manufactures and technology adopters
 - IDMs
 - Fabless
 - EDS
- FO processes bridged the reliability gap for CSP FI, P-WLCSP is proposed as the approach that will provide the die level building blocks needed for advanced multi-chip packaging solutions

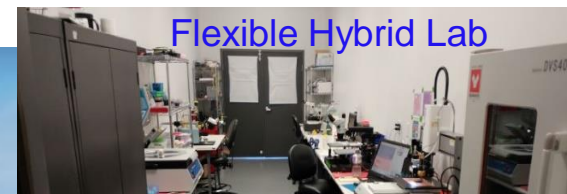


American Semiconductor is the industry leader in ultra-thin advanced packaging. We develop state-of-the-art ultra-thin electronics technology.

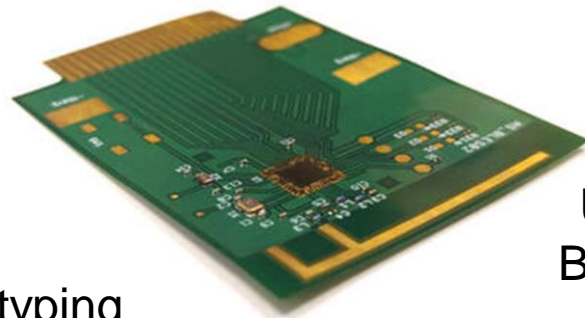


- Founded Nov. 2001
- Over 21 SBIR wins
- 2-time Boeing SOTY

Member:



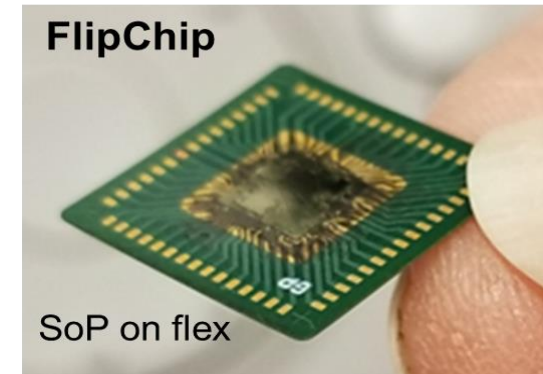
Commercializing Semiconductor-on-Polymer™ (SoP™) technology for dual-use production



Ultra-thin
Bluetooth®

SoP Chips for prototyping

| Product | Description |
|---------------------|---|
| AS_ADC100x | FleX-ADC Analog-to-Digital Converter: 8-channels, 8-bits ASI (TowerJazz Semiconductor Foundry) |
| AS_ADC2001 | FleX-ADC Analog-to-Digital Converter with 3 Configurable Op Amps ASI (TowerJazz Semiconductor Foundry) |
| AS_CY820x | FleX-SoC (System-on-a-Chip) with Capacitive Sense Cypress Semiconductor PSOC® CY8C20XX6A/S |
| AS_EM4325P | FleX-RFID 900MHz RFID Communication Temperature Monitoring IC EM Microelectronics EM4325 |
| AS_NHS3100P | FleX-NFC Temp Logging IC with ARM® Cortex-M0+ NXP Semiconductor NTAG SmartSensor with Temperature Sensor |
| AS_AM39513 | FleX-NFC Sensor Tag IC AMS (Austria Microsystems) AS39513 NFC Sensor Tag IC |
| AS_OPA4002 | FleX-OpAmp Quad High Performance Op Amps ASI (TowerJazz Semiconductor Foundry) |
| AS_OPA4003 | FleX-OpAmp Quad Output Transconductance Op Amps ASI (TowerJazz Semiconductor Foundry) |
| AS_CY8C424 | FleX-BLE Bluetooth Low Energy with ARM® Cortex-M0 Cypress Semiconductor PSOC® 4 Bluetooth LE |
| AS_NRF51822 | FleX-BLE Bluetooth Low Energy with ARM® Cortex-M0 Nordic Semiconductor nRF51822 |
| Customer SoP | Additional customer specific wafers are being packaged in SoP CSP |



SoP NFC Chips and Assemblies



Thank You

**SoP packaging supported in part through
Joint Development with HD MicroSystems**



**Special thanks to Disco for their on-going
support of special processing requirements**



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